

AMENDMENTS TO THE ABSTRACT:

Please replace the abstract with the following amended abstract:

Provided is a method of depositing a thin film using a hafnium compound. ~~In this~~
~~The method, the depositing (S200) of a thin film includes (S20)~~depositing a primary thin
film and (S21)depositing a secondary thin film. ~~Step (S200) is performed by repeating~~
~~steps (S20) and (S21)~~The depositing of the primary thin film and the depositing of the
secondary thin film are repeated once or more. ~~Step (S20)~~The depositing of the primary
thin film includes (S20-1)feeding a first reactive gas, ~~(S20-2)~~purging the first reactive
gas, ~~(S20-3)~~feeding a third reactive gas, and ~~(S20-4)~~purging the third reactive gas, and
repeats the steps N times. The feeding of the first reactive gas Step (S21) includes (S21-
~~1)~~feeding a second reactive gas, ~~(S21-2)~~purging the second reactive gas, ~~(S21-3)~~
feeding the third reactive gas, and ~~(S21-4)~~purging the third reactive gas, and repeats the
steps. ~~Step (S20) is performed by repeating steps (S20-1), (S20-2), (S20-3), and (S20-4)~~
~~N times, and step (S21) is performed by repeating steps (S21-1), (S21-2), (S21-3), and~~
~~(S21-4) M times.~~